

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	54.6598	N/A	48.1248
RT2	16.8142	N/A	12.9503
RT3	71.2893	N/A	8.6500
RT4	77.3114	N/A	30.2749
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	1.2876	N/A	592.9211 u
CT2	41.6505 u	N/A	49.6255 u
CT3	8.5760 m	N/A	265.2869 m
CT4	646.3112 u	N/A	2.9450 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	19.9328	N/A	15.0822
RF2	84.8053	N/A	69.9790
RF3	61.9463	N/A	627 m
RF4	53.3156	N/A	14.3211
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	50.2926 u	N/A	38.5493 u
CF2	552.5404 u	N/A	485.7156 u
CF3	8.9781 m	N/A	21.1471 m
CF4	1.3229	N/A	26.8661 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

